

# RBV800D - RBV810D

**PRV : 50 - 1000 Volts**

**Io : 8.0 Amperes**

## FEATURES :

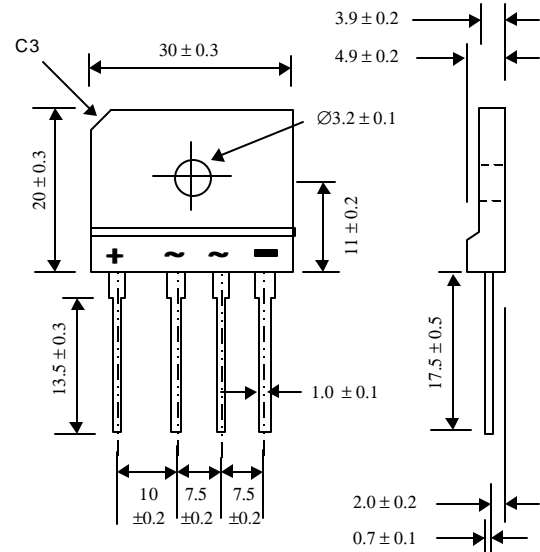
- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* High case dielectric strength of 2000 V<sub>DC</sub>
- \* Ideal for printed circuit board
- \* Very good heat dissipation

## MECHANICAL DATA :

- \* Case : Reliable low cost construction utilizing molded plastic technique
- \* Epoxy : UL94V-O rate flame retardant
- \* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Polarity symbols marked on case
- \* Mounting position : Any
- \* Weight : 7.7 grams

# SILICON BRIDGE RECTIFIERS

## RBV25



**Dimensions in millimeters**

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV 800D	RBV 801D	RBV 802D	RBV 804D	RBV 806D	RBV 808D	RBV 810D	UNIT
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Current T <sub>c</sub> = 55°C	I <sub>F(AV)</sub>	8.0							Amps.
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	300							Amps.
Current Squared Time at t < 8.3 ms.	I <sup>2</sup> <sub>t</sub>	166							A <sup>2</sup> S
Maximum Forward Voltage per Diode at I <sub>F</sub> = 8.0 Amps.	V <sub>F</sub>	1.0							Volts
Maximum DC Reverse Current Ta = 25 °C	I <sub>R</sub>	10							μA
at Rated DC Blocking Voltage Ta = 100 °C	I <sub>R(H)</sub>	200							μA
Typical Thermal Resistance (Note 1)	R <sub>θJC</sub>	2.2							°C/W
Typical Thermal Resistance at Junction to Ambient	R <sub>θJA</sub>	15							°C/W
Operating Junction Temperature Range	T <sub>J</sub>	- 40 to + 150							°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150							°C

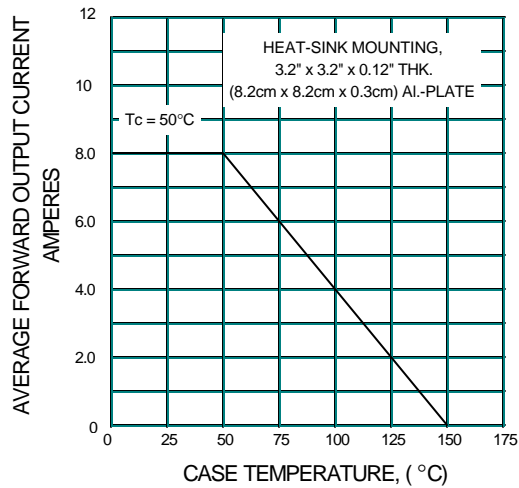
## Notes :

1. Thermal Resistance from junction to case with units mounted on a 3.2"x3.2"x0.12" THK (8.2cm.x8.2cm.x0.3cm.) Al. Plate. heatsink.

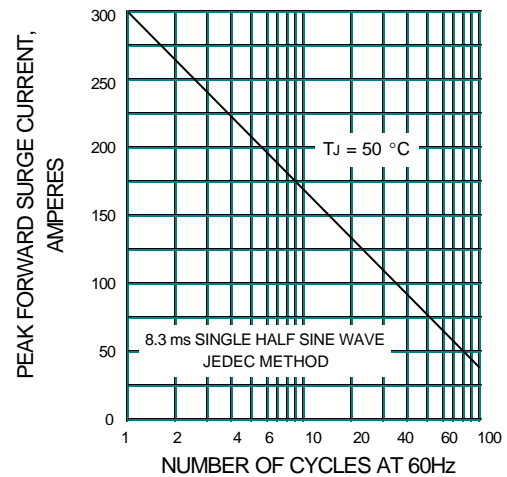
**UPDATE : AUGUST 3. 1998**

## RATING AND CHARACTERISTIC CURVES ( RBV800D - RBV810D )

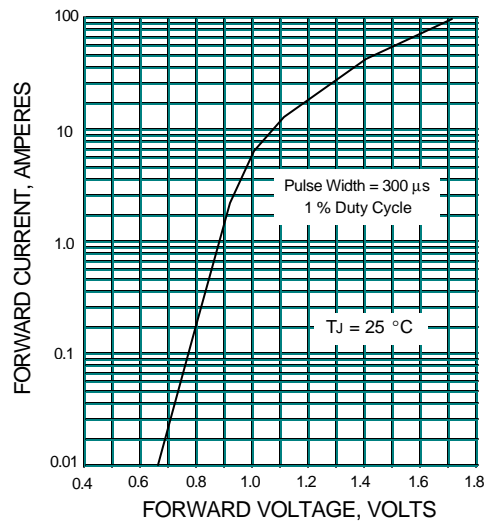
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE**

